CHENMKO ENTERPRISE CO.,LTD

CH3906MPT

Lead free devices

SURFACE MOUNT
PNP Switching Transistor

VOLTAGE 40 Volts CURRENT 0.2 Ampere

APPLICATION

* Telephony and proferssional communction equipment.
* Other switching applications.

FEATURE

* Small surface mounting type. (SOT-723)
* Low current (Max.=200mA).
* Suitable for high packing density.
* Low voltage (Max.=40V) .
* High saturation current capability.
* Voltage controlled small signal switch.

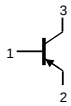
CONSTRUCTION

* PNP Switching Transistor

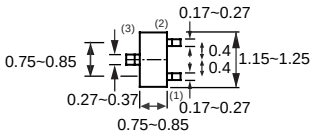
MARKING

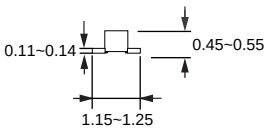
* 37

CIRCUIT



SOT-723





Dimensions in millimeters

SOT-723

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	-40	V
V_{CEO}	collector-emitter voltage	open base	–	-40	V
V_{EBO}	emitter-base voltage	open collector	–	-5	V
I_C	collector current DC		–	-200	mA
I_{CM}	peak collector current		–	-200	mA
I_{BM}	peak base current		–	-100	mA
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC CURVES (CH3906MPT)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise speciÞed.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = - 30 V	–	-50	nA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = 6 V	–	-50	nA
h_{FE}	DC current gain	V_{CE} = -1V; note 1			
		I_C = -0.1mA	60	–	
		I_C = -1mA	80	–	
		I_C = -10 mA	100	300	
		I_C = - 50 mA	60	–	
		I_C = -100 mA	30	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = -10 mA; I_B = - 1 mA	–	-250	mV
		I_C = -50 mA; I_B = - 5 mA	–	-400	mV
V_{BEsat}	base-emitter saturation voltage	I_C = -10 mA; I_B = -1mA	-650	-850	mV
		I_C = -50 mA; I_B = - 5 mA	–	-950	mV
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = - 5 V ; f = 1 MHz	–	4.5	pF
C_e	emitter capacitance	$I_C = i_c$ = 0; V_{EB} = -500 mV; f = 1 MHz	–	10	pF
f_T	transition frequency	I_C = 10 mA; V_{CE} = - 20 V ; f = 100 MHz	250	–	MHz
F	noise Þgure	I_C = 100 µA; V_{CE} = - 5 V; R_S = 1 kΩ; f = 10 Hz to 15.7 kHz	–	4	dB
Switching times (between 10% and 90% levels);					
t_{on}	turn-on time	I_{Con} = -10 mA; I_{Bon} = -1 mA; I_{Boff} = 1 mA	–	65	ns
t_d	delay time		–	35	ns
t_r	rise time		–	35	ns
t_{off}	turn-off time		–	300	ns
t_s	storage time		–	225	ns
t_f	fall time		–	75	ns

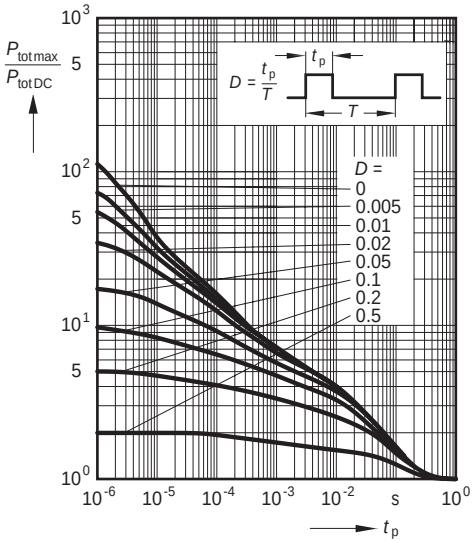
Note

1. Pulse test: $t_p \leq 300\ \mu s$; $\delta \leq 0.02$.

RATING CHARACTERISTIC CURVES (CH3906MPT)

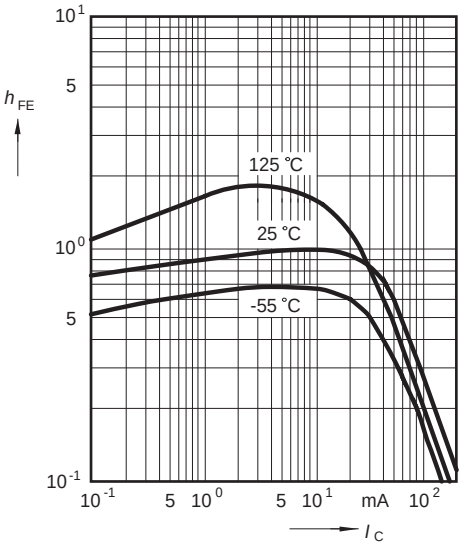
Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$



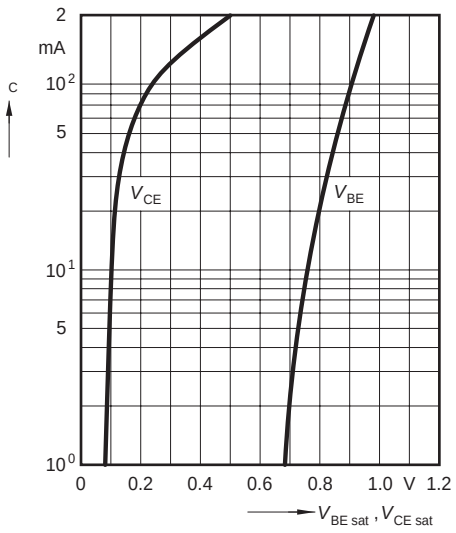
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 1 V, normalized



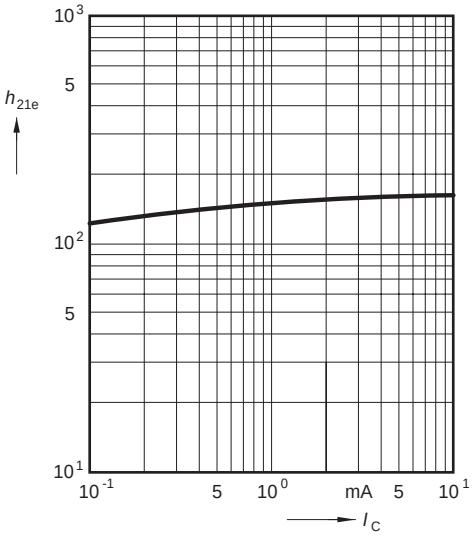
Saturation voltage $I_C = f(V_{BEsat}; V_{CEsat})$

h_{FE} = 10



Short-circuit forward current transfer ratio $h_{21e} = f(I_C)$

V_{CE} = 10V, f = 1MHz

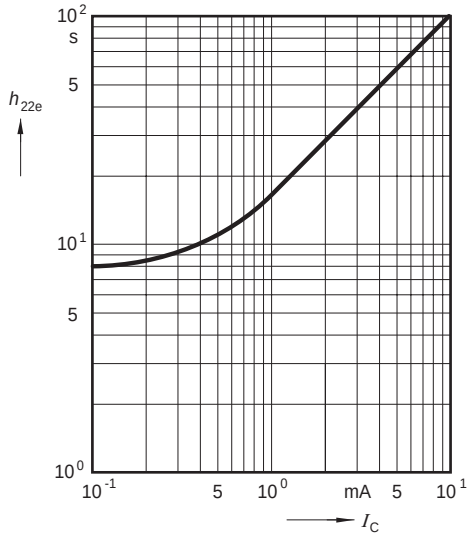


RATING CHARACTERISTIC CURVES (CH3906MPT)

Open-circuit output admittance

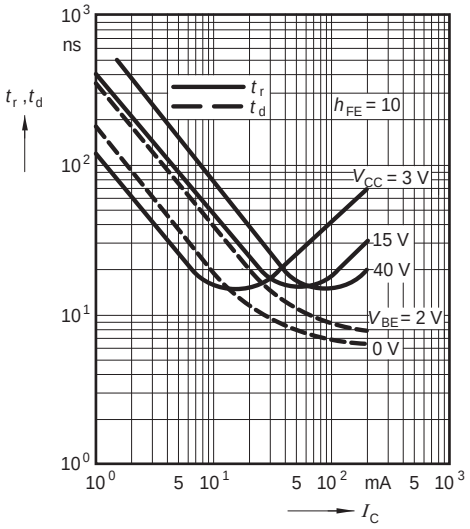
$h_{22e} = f(I_C)$

V_{CE} = 10V, f = 1MHz

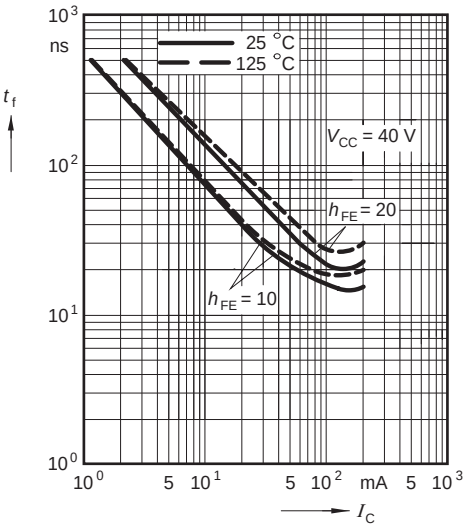


Delay time $t_d = f(I_C)$

Rise time $t_r = f(I_C)$



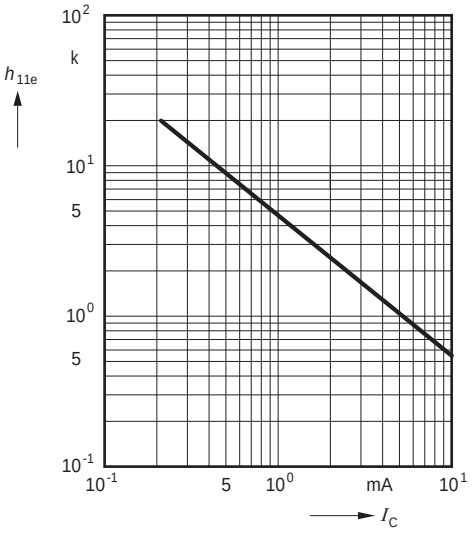
Fall time $t_f = f(I_C)$



Input impedance

$h_{11e} = f(I_C)$

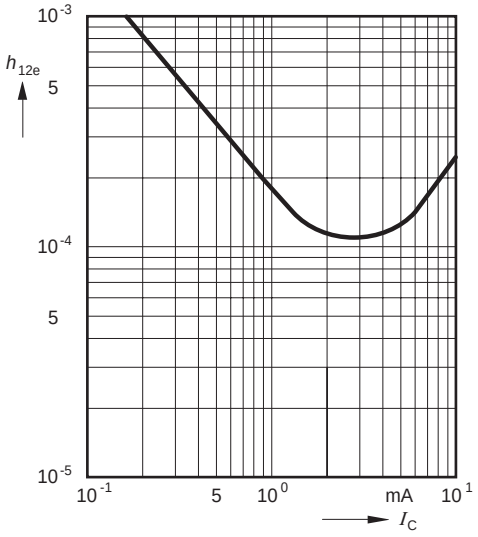
V_{CE} = 10 V, f = 1kHz



RATING CHARACTERISTIC CURVES (CH3906MPT)

Open-circuit reverse voltage transfer ratio $h_{12e} = f(I_C)$

V_{CE} = 10V, f = 1kHz



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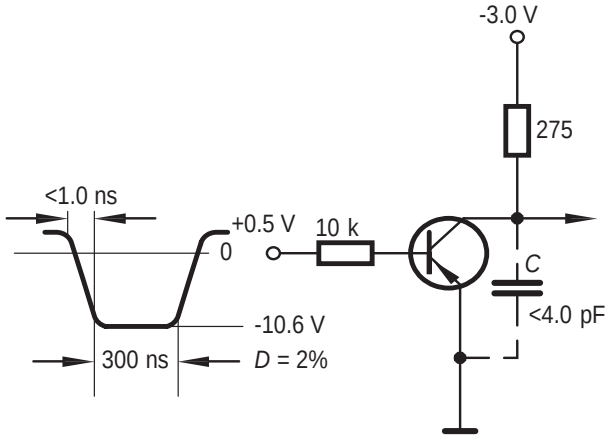
Test circuit

Delay and rise time



Storage and fall time